

				Sub	ject	Coc	le: K	OF	<i>1</i> 048
Roll No:									

Printed Page: 1 of 2

BTECH (SEM IV) THEORY EXAMINATION 2023-24 ELECTRONICS ENGINEERING

TIME: 3 HRS M.MARKS: 100

Note: 1. Attempt all Sections. If require any missing data, then choose suitably.

SECTION A

1.	Attempt all questions in brief.					
Q no.	Question	Marks	CO			
a.	List and define the various capacitances of diode.	02	1			
b.	Differentiate between n type and p type semiconductors.	02	1			
c.	Define voltage regulators.	02	2			
d.	List the applications of tunnel diode.	02	2			
e.	State the reason of choosing voltage divider biasing as best suitable	02	3			
	choice.					
f.	Differentiate between AC and DC analysis of a circuit.	02	3			
g.	List the properties of an ideal operational amplifier.	02	4			
h.	Define CMRR and input offset voltage.	02	4			
i.	Define sweep voltage.	02	5			
j.	List the applications of digital multimeter.	02	5			

SECTION B

2.	Attempt any three of the following:	3 x 10	=30
Q no.	Question	Marks	CO
a.	Explain the p-n junction working with no bias, forward bias and reverse bias.	70	1
b.	Discuss the voltage multiplier circuit using diodes in detail.	10	2
c.	Derive the input impedance, output impedance and voltage gain of common emitter amplifier without emitter resistance through AC analysis of it.	10	3
d.	Discuss the following circuits using operational amplifier using relevant mathematical expressions: 1. Differentiator 2. Integrator 3. Summing amplifier 4. Difference amplifier	10	4
e.	Discuss the working the CRO using the block diagram. Also explain the frequency and phase measurement using CRO.	10	5

SECTION C

3.	3. Attempt any <i>one</i> part of the following:					
Q no.	Question	Marks	CO			
a.	Discuss and differentiate between Zener breakdown mechanism and avalanche breakdown mechanism.	10	1			
b.	Define doping. Also explain the process of making an intrinsic semiconductor to extrinsic semiconductor along with the differentiation between intrinsic and extrinsic semiconductor.	10	1			



				Sub	ject	Coc	le: k	(OF	<u> 2048</u>
Roll No:									

BTECH (SEM IV) THEORY EXAMINATION 2023-24 ELECTRONICS ENGINEERING

TIME: 3 HRS M.MARKS: 100

4.	Attempt any one part of the following:	1 x 10	= 10
Q no.	Question	Marks	CO
a.	Assume the diodes to be ideal. Find the range of input for which the output is not clipped. 10k 10k 10k 10k 10k 10k 10k	10	2
b.	Discuss the followings: 1. Light emitting diodes 2. Varactor diodes	10	2

5. Attempt any *one* part of the following:

	10		()

Printed Page: 2 of 2

Q no.	Question	Marks	CO
a.	Discuss the construction and working of depletion type and enhancement type MOSFET with their input, output and transfer characteristics.	10	3
b.	Discuss the various biasing schemes used for BJT.	10	3

6. Attempt any *one* part of the following:

1	X	1	() =	: 1(

Q no.	Question	Marks	CO
a.	Explain the block diagram of operational amplifier and hence	10	4
	differentiate between ideal and practical operational amplifiers.		
b.	Design the following circuits using operational amplifier:	10	4
	1. Unity gain amplifier		
	2. Non inverting amplifier having gain of 11		
	3. Inverting amplifier having gain 10		

7. Attempt any *one* part of the following:

1	X	10) =	10
_			•	

Q no.	Question	Marks	CO
a.	Using suitable diagram explain the basic principle of digital multimeter.	10	5
b.	Compare between digital storage oscilloscope and analog oscilloscope.	10	5